

CORRECTION

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Correction: Aliovalent A-site engineered AgNbO₃ lead-free antiferroelectric ceramics toward superior energy storage density

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Correction for 'Aliovalent A-site engineered AgNbO₃ lead-free antiferroelectric ceramics toward superior energy storage density' by Nengneng Luo *et al.*, *J. Mater. Chem. A*, 2019, DOI: 10.1039/c9ta02053e.

The authors regret an error in the published article. The phrase “In contrast, the $\Delta G_{\text{FE-AFE}}$ for the FE-to-AFE phase transition is flattened, corresponding to decreased E_A ” should instead have read as follows: “The $\Delta G_{\text{FE-AFE}}$ for the FE-to-AFE phase transition, in contrast, is flattened, which also contributes to increased E_A ”.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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